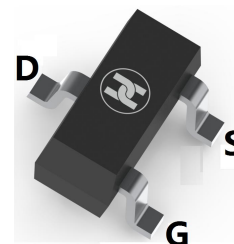


N-CHANNEL MOSFET

FEATURES

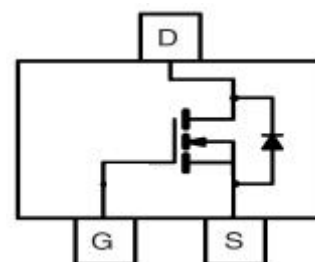
- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching



SOT-23

MECHANICAL DATA

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Weight: 0.008 grams (approximate)



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	1.2	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	0.93	
I_{DM}	Pulsed Drain Current ①	7.3	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	540	mW
	Linear Derating Factor	4.3	mW/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

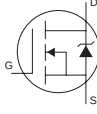
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	230	°C/W

N-CHANNEL MOSFET
Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.029	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.25	Ω	$V_{GS} = 10V, I_D = 0.91A$ ③
		—	—	0.40		$V_{GS} = 4.5V, I_D = 0.46A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	0.87	—	—	S	$V_{DS} = 10V, I_D = 0.46A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	3.3	5.0	nC	$I_D = 0.91A$
Q_{gs}	Gate-to-Source Charge	—	0.48	0.72		$V_{DS} = 24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.1	1.7		$V_{GS} = 10V$, See Fig. 6 and 9 ③
$t_{d(on)}$	Turn-On Delay Time	—	3.9	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	4.0	—		$I_D = 0.91A$
$t_{d(off)}$	Turn-Off Delay Time	—	9.0	—		$R_G = 6.2\Omega$
t_f	Fall Time	—	1.7	—		$R_D = 16\Omega$, See Fig. 10 ③
C_{iss}	Input Capacitance	—	85	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	34	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	15	—		$f = 1.0\text{MHz}$, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	0.54	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	7.3		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 0.91A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	26	40	ns	$T_J = 25^\circ\text{C}, I_F = 0.91A$
Q_{rr}	Reverse Recovery Charge	—	22	32	nC	$di/dt = 100A/\mu s$ ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② $I_{SD} \leq 0.91A$, $di/dt \leq 120A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ Surface mounted on FR-4 board, $t \leq 5\text{sec}$.

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Typical Characteristics

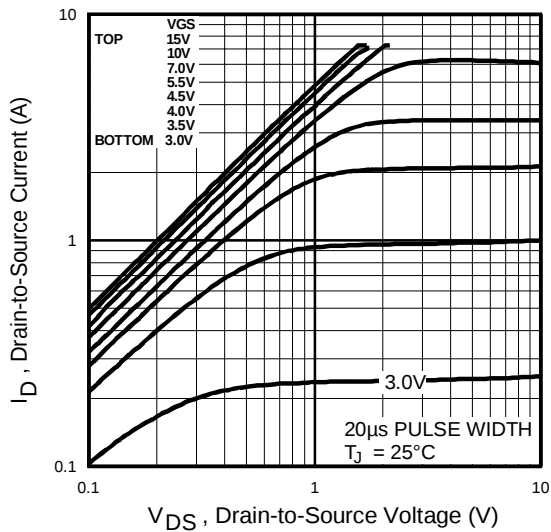


Fig 1. Typical Output Characteristics

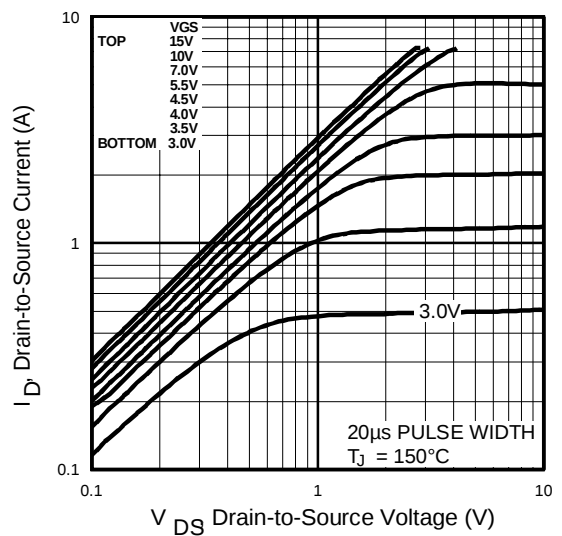


Fig 2. Typical Output Characteristics

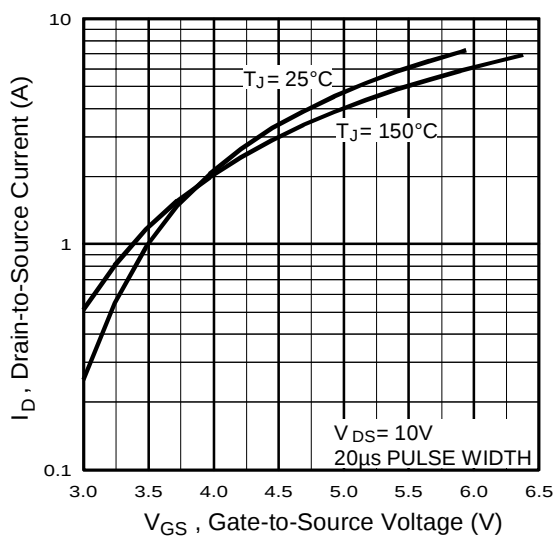


Fig 3. Typical Transfer Characteristics

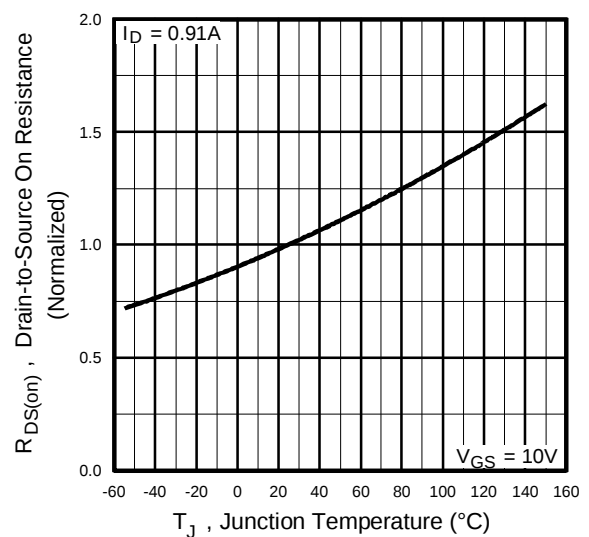


Fig 4. Normalized On-Resistance Vs. Temperature

N-CHANNEL MOSFET

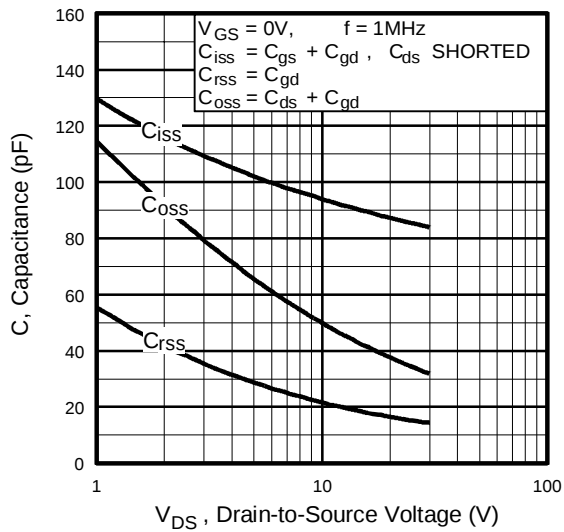


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

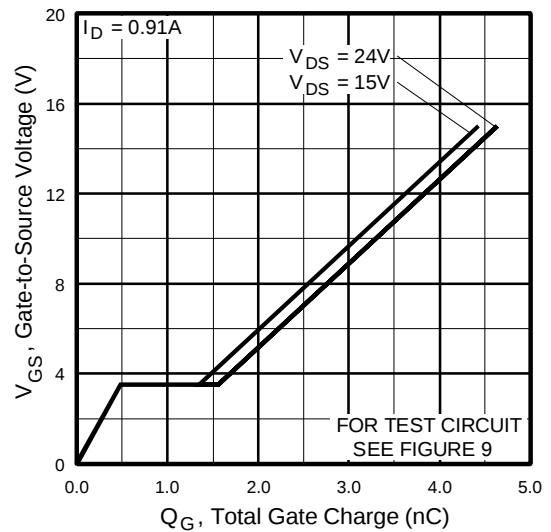


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

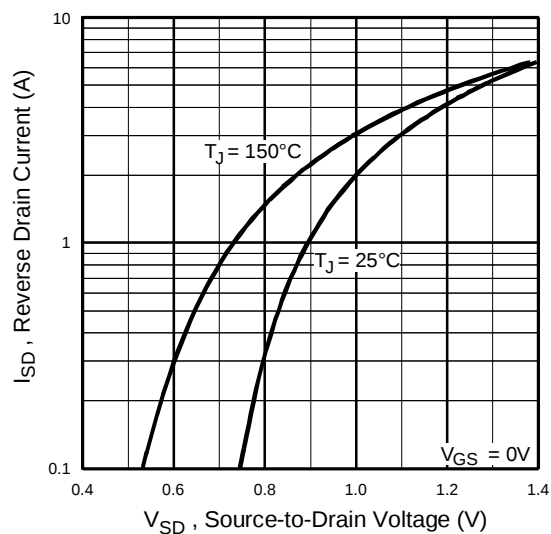


Fig 7. Typical Source-Drain Diode Forward Voltage

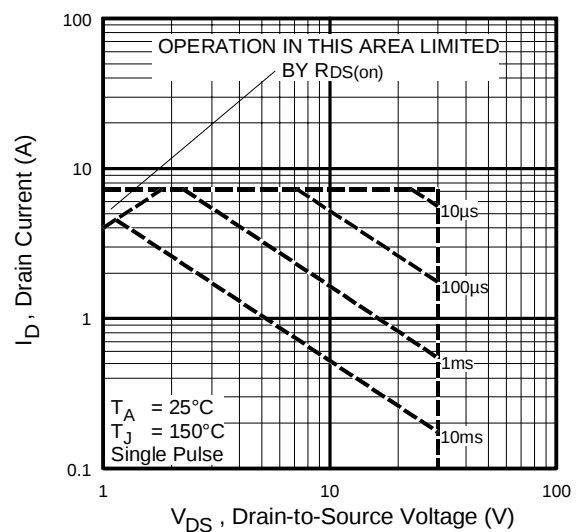


Fig 8. Maximum Safe Operating Area

N-CHANNEL MOSFET

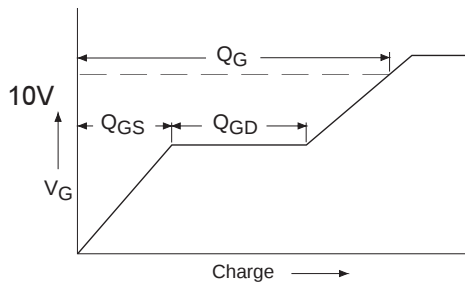


Fig 9a. Basic Gate Charge Waveform

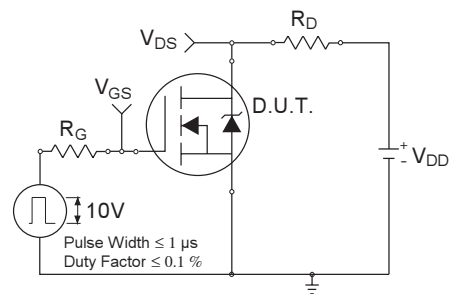


Fig 10a. Switching Time Test Circuit

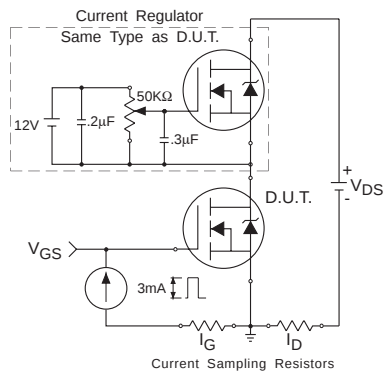


Fig 9b. Gate Charge Test Circuit

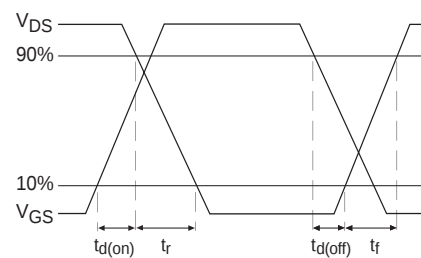


Fig 10b. Switching Time Waveforms

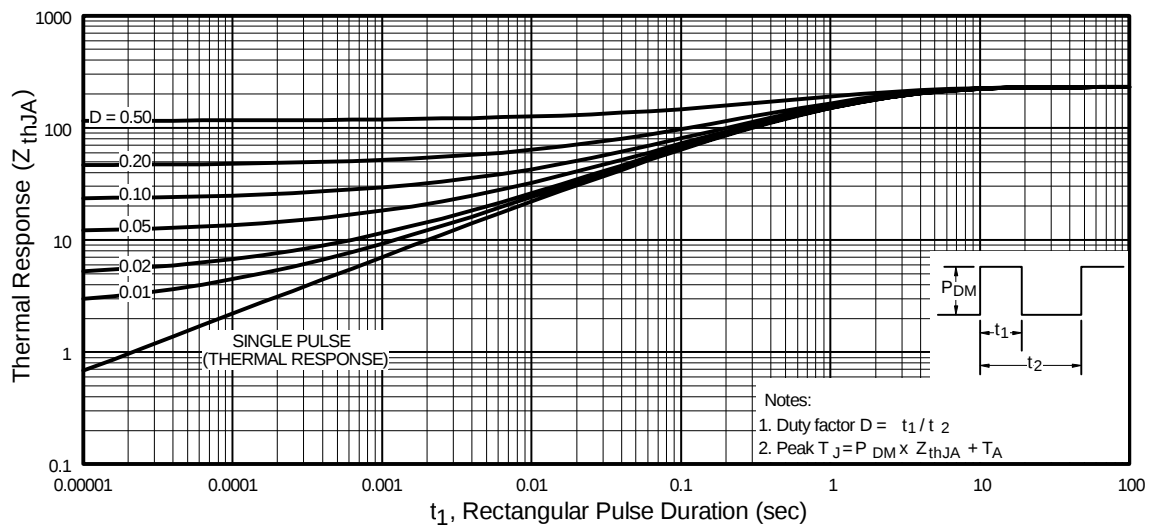


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

N-CHANNEL MOSFET

Peak Diode Recovery dv/dt Test Circuit

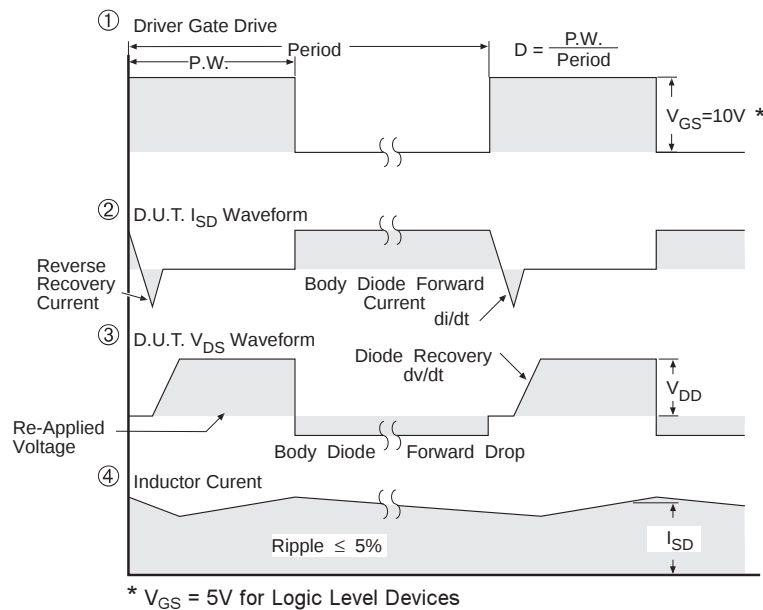
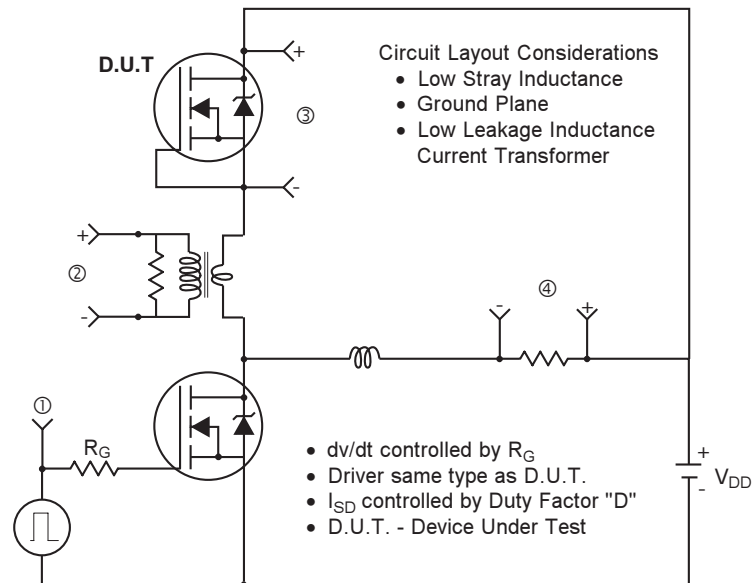
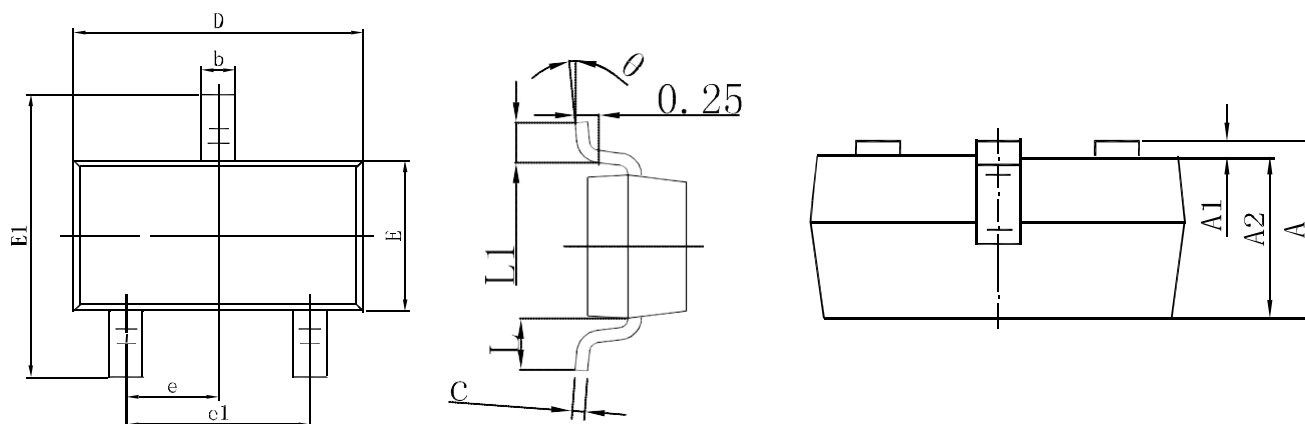


Fig 12. For N-Channel HEXFETS

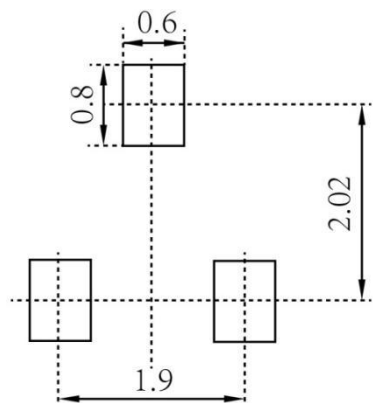
N-CHANNEL MOSFET

SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



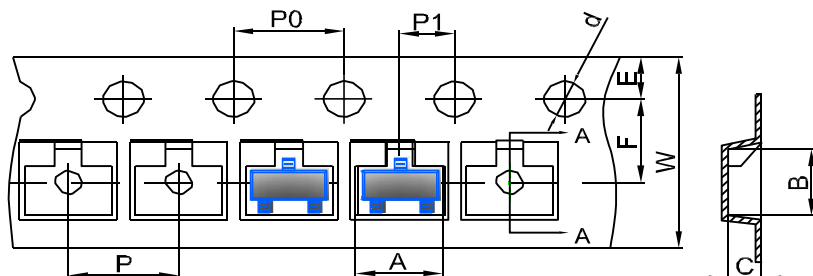
Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

N-CHANNEL MOSFET

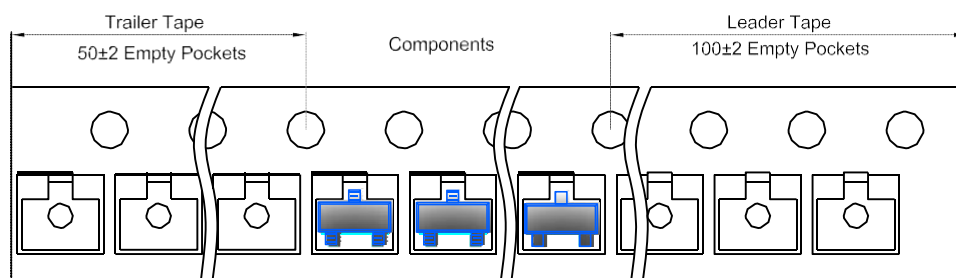
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

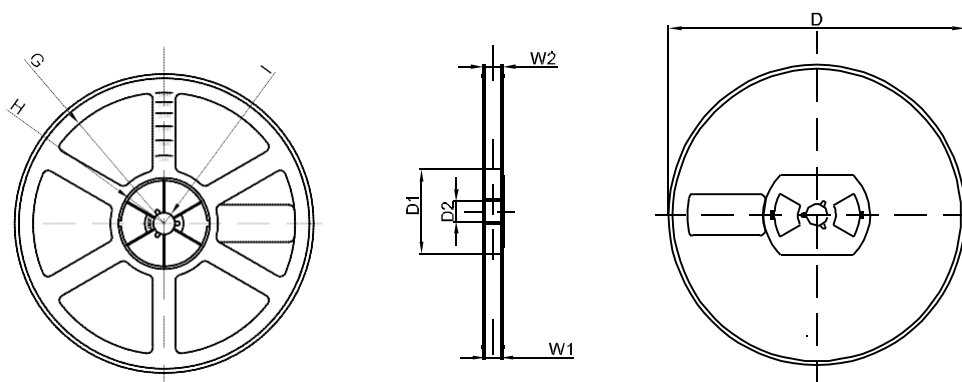


	DIMENSIONS ARE IN MILLIMETER									
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer



SOT-23 Reel



	DIMENSIONS ARE IN MILLIMETER							
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1